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Development Status of Type II Superlattice Infrared Detector in JAXA

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We present the development status of a Type II superlattice (T2SL) infrared detector for future space applications in JAXA. InAs/GaSb T2SL is the only known infrared material that has a theoretically predicted higher performance than HgCdTe. We first fabricated a single-pixel detector with a cutoff wavelength of 6 μ m. The detector is a pin photodiode with a superlattice consisting of 9 InAs monolayers (MLs) and 7 GaSb MLs. The dark current density of the detector is 1.8×10^{-4} A/cm² at a bias voltage of -100 mV. We also present the results of an optical evaluation of the detector. The cutoff wavelength is 5.5 μ m at 30 K. The responsivity is 0.3 ± 0.05 A/W at 4.5 μ m. We also show the development of an array detector with a cutoff wavelength of 6 μ m. However, further improvements are required for developing array detectors with longer cutoff wavelengths.

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